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Silicon PNP transistor in a SOT-323 Plastic Package.

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Complements the MMBTA06W.

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General purpose amplifier.

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PIN1 Emitter PIN 2 Base PIN 3 Collector

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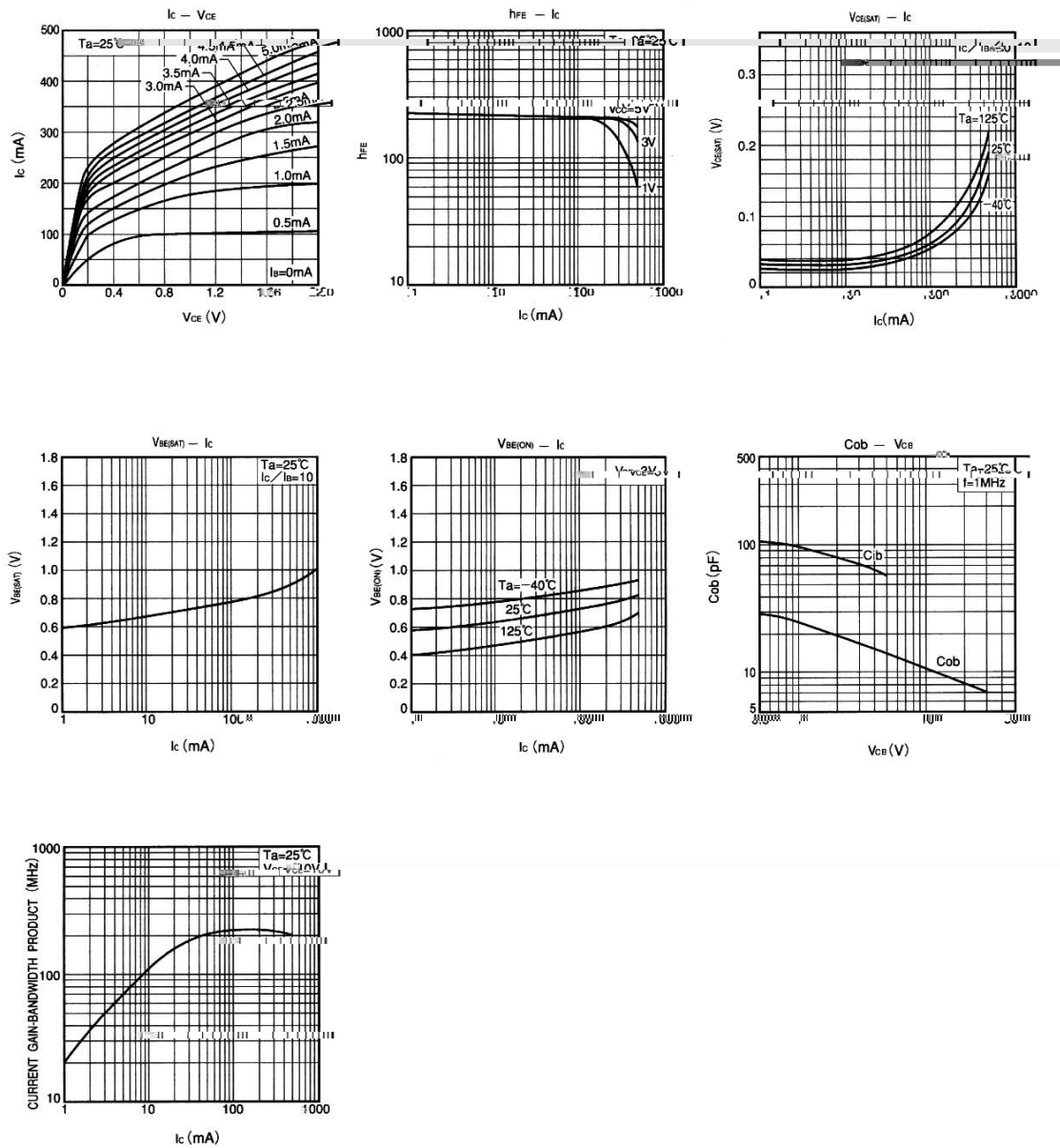
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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-0.5	A
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-80			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -80V$ $I_E = 0$			-0.1	μA
Emitter Cut-Off Current	I_{CEO}	$V_{CB} = -60V$ $I_B = 0$			-1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{BE} = -4.0V$ $I_C = 0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -1.0V$ $I_C = -100mA$	100			
	$h_{FE(2)}$	$V_{CE} = -1.0V$ $I_C = -10mA$	100			

Collector to Emitter Saturation

3A'EV f



尺寸标注

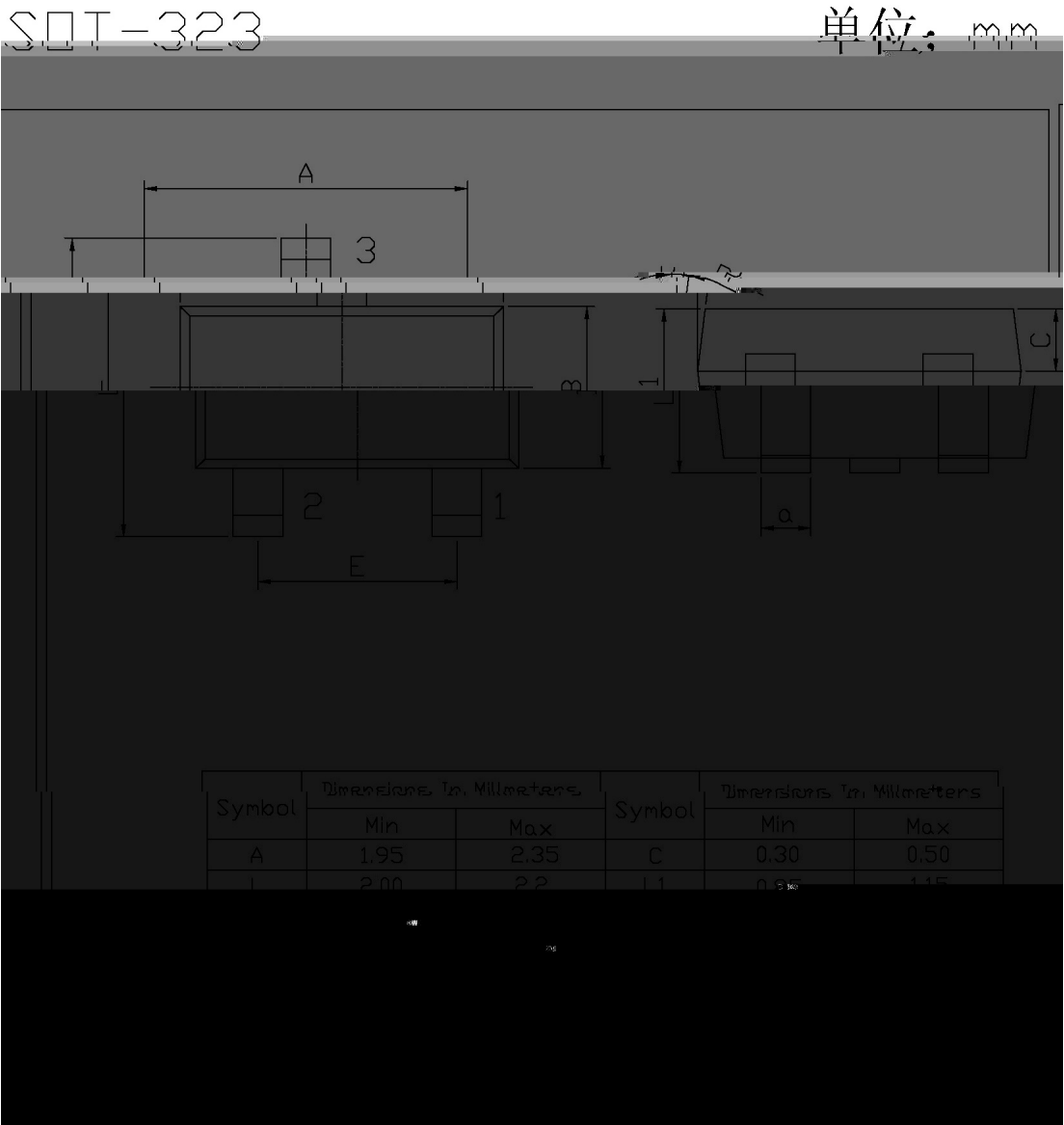


图 2



H

R2G

Note:

H: Company Code.

R2G: Product Type Code



260 20

90sec.

5 0.5sec.



sec



(unit: mm ³)
Outer Box 箱
390×385×205